



DMN15H310SE

150V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| V _{(BR)DSS} | R _{DS(ON)} max | I _D T _A = +25°C | |
|----------------------|---|--|--|
| 150V | $310 \text{m}\Omega$ @ $V_{GS} = 10 \text{V}$ | 2.0A | |
| | 330mΩ @ V _{GS} = 5.0V | 1.9A | |

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Transformer Driving Switch
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Features

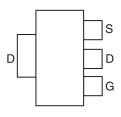
- 100% Unclamped Inductive Switch (UIS) Test in Production
- · Fast Switching Speed
- Low On-Resistance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

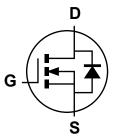
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 63
- Weight: 0.112 grams (Approximate)







Pin Out - Top View



Equivalent Circuit

Ordering Information (Note 4)

| Part Number | Compliance | Case | Packaging |
|----------------|------------|--------|---------------------|
| DMN15H310SE-13 | Standard | SOT223 | 2,500 / Tape & Reel |

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

O!! = Manufacturer's Marking 15H310 = Marking Code YWW = Date Code Marking Y or Y= Year (ex: 4 = 2014) WW = Week (01 - 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Units | |
|---|------------------|----------------|------------|---|
| Drain-Source Voltage | V _{DSS} | 150 | V | |
| Gate-Source Voltage | V _{GSS} | ±20 | V | |
| Continuous Drain Current (Note 5) V_{GS} = 10V $ T_A = +25^{\circ}C $ $T_C = +70^{\circ}C $ $T_C = +70^{\circ}C $ | | I _D | 2.0 1.6 | А |
| | | I _D | 7.1 5.6 | А |
| Pulsed Drain Current (10µs pulse, duty cycle = 1%) | I _{DM} | 10 | Α | |
| Maximum Body Diode Continuous Current | Is | 2.5 | Α | |
| Avalanche Energy (Note 6) L=26mH | Eas | 1.45 | mJ | |
| Avalanche Current (Note 6) L=26mH | I _{AS} | 0.2 | Α | |
| Peak Diode Recovery dv/dt ($I_{SD} \le 7.3A$, di/dt $\le 300A/\mu s$) | dv/dt | 5 | V/ns | |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Units | | |
|--|-----------------------------------|----------------|-------|-----|--|
| Total Power Dissipation (Note 5) | TA = +25°C | D- | 1.9 | W | |
| Total Fower Dissipation (Note 5) | TA = +70°C | P _D | 1.2 |] " | |
| Thermal Resistance, Junction to Ambient (Note 5) | R _{θJA} | 64 | °C/W | | |
| Total Power Dissipation (Note 5) TC = +25°C | | P _D | 23.5 | W | |
| Thermal Resistance, Junction to Case (Note 5) | R ₀ JC | 5.3 | °C/W | | |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C | | |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|--|----------------------|-----|------|------|------|--|--|
| OFF CHARACTERISTICS (Note 7) | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 150 | _ | _ | V | $V_{GS} = 0V, I_D = 250\mu A$ | |
| Zero Gate Voltage Drain Current | I _{DSS} | _ | _ | 1 | μΑ | V _{DS} = 120V, V _{GS} = 0V | |
| Gate-Source Leakage | I _{GSS} | _ | _ | ±100 | nA | $V_{GS} = \pm 20V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 7) | | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | 1 | 2.2 | 3 | V | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | |
| Static Drain-Source On-Resistance | В | _ | 178 | 310 | mΩ | V _{GS} = 10V, I _D = 1.5A | |
| Static Drain-Source On-Resistance | R _{DS (ON)} | _ | 190 | 330 | | V _{GS} = 5.0V, I _D = 1.0A | |
| Diode Forward Voltage | V _{SD} | _ | 0.76 | 1.2 | V | V _{GS} = 0V, I _S = 1.7A | |
| DYNAMIC CHARACTERISTICS (Note 6) | | | | | | | |
| Input Capacitance | C _{iss} | _ | 405 | _ | | V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz | |
| Output Capacitance | Coss | _ | 40 | _ | pF | | |
| Reverse Transfer Capacitance | C _{rss} | _ | 20 | _ | | | |
| Gate Resistance | R _G | _ | 2.88 | _ | Ω | V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz | |
| Total Gate Charge (V _{GS} = 5.0V) | Qg | _ | 4.6 | _ | | | |
| Total Gate Charge (V _{GS} = 10V) | Qg | _ | 8.7 | _ | | | |
| Gate-Source Charge | Q _{gs} | _ | 1.7 | _ | nC | $V_{DS} = 80V, I_D = 7.3A$ | |
| Gate-Drain Charge | Q _{gd} | _ | 1.8 | _ | | | |
| Turn-On Delay Time | t _{D(on)} | _ | 3.5 | _ | | $V_{DD} = 50V, V_{GS} = 10V,$ $R_G = 25\Omega, I_D = 7.3A$ | |
| Turn-On Rise Time | t _r | _ | 7.8 | _ | nS | | |
| Turn-Off Delay Time | t _{D(off)} | _ | 22 | _ | 113 | | |
| Turn-Off Fall Time | t _f | _ | 11 | _ | | | |
| Reverse Recovery Time | t _{rr} | _ | 38 | _ | ns | I _F = 7.3A, di/dt = 100A/μs | |
| Reverse Recovery Charge | Q _{rr} | _ | 53 | _ | nC | I _F = 7.3A, di/dt = 100A/μs | |

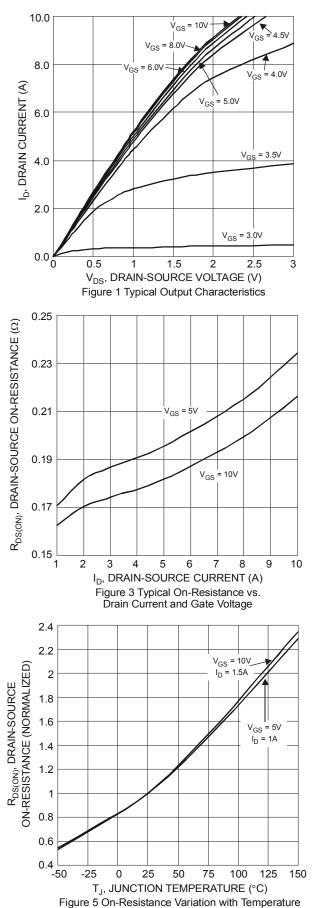
5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

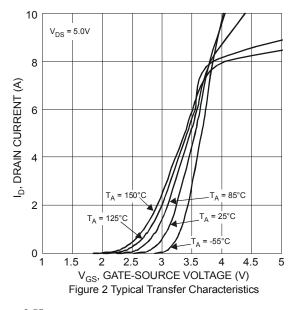
Notes:

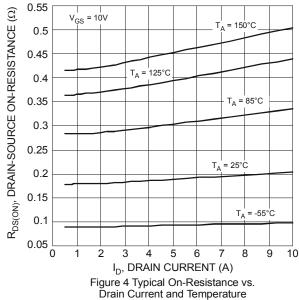
^{6.} Guaranteed by design. Not subject to product testing.7. Short duration pulse test used to minimize self-heating effect.











0.45 $R_{DS(ON)}$, DRAIN-SOURCE ON-RESISTANCE (Ω) 0.4 0.35 0.3 = 10V 0.25 V_{GS} I_D = 1.5A 0.2 0.15 0.1 0.05 -50 -25 25 50 125 0 75 100 T_{.I}, JUNCTION TEMPERATURE (°C) Figure 6 On-Resistance Variation with Temperature



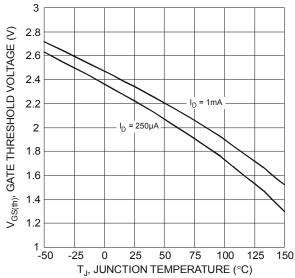
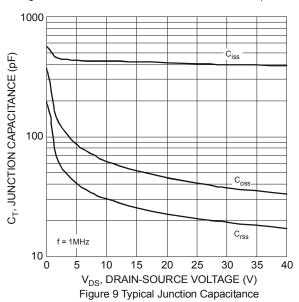
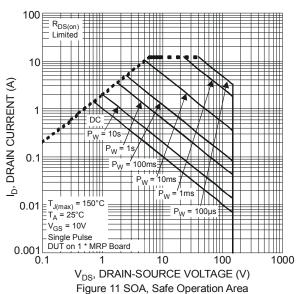
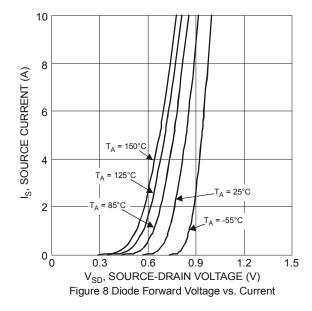
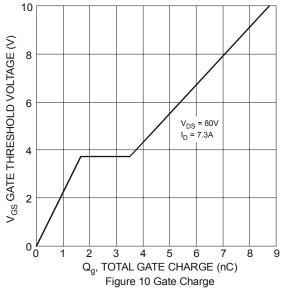


Figure 7 Gate Threshold Variation vs. Ambient Temperature

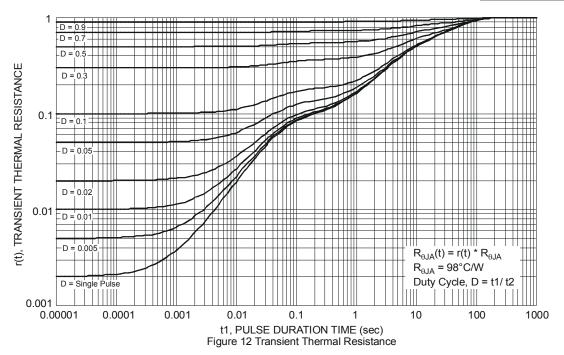








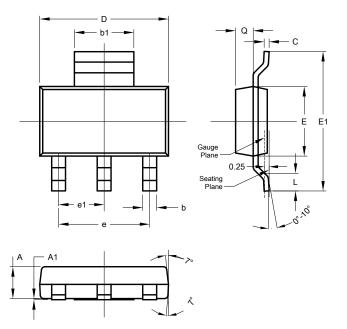






Package Outline Dimensions

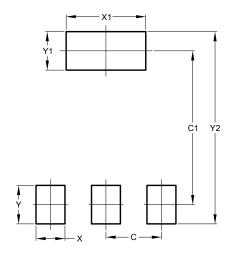
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



| SOT223 | | | | | |
|----------------------|-------|------|------|--|--|
| Dim | Min | Max | Тур | | |
| Α | 1.55 | 1.65 | 1.60 | | |
| A1 | 0.010 | 0.15 | 0.05 | | |
| b | 0.60 | 0.80 | 0.70 | | |
| b1 | 2.90 | 3.10 | 3.00 | | |
| С | 0.20 | 0.30 | 0.25 | | |
| D | 6.45 | 6.55 | 6.50 | | |
| Е | 3.45 | 3.55 | 3.50 | | |
| E1 | 6.90 | 7.10 | 7.00 | | |
| е | - | - | 4.60 | | |
| e1 | - | - | 2.30 | | |
| L | 0.85 | 1.05 | 0.95 | | |
| Q | 0.84 | 0.94 | 0.89 | | |
| All Dimensions in mm | | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) | | |
|------------|---------------|--|--|
| С | 2.30 | | |
| C1 | 6.40 | | |
| Х | 1.20 | | |
| X1 | 3.30 | | |
| Υ | 1.60 | | |
| Y1 | 1.60 | | |
| C2 | 8.00 | | |



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